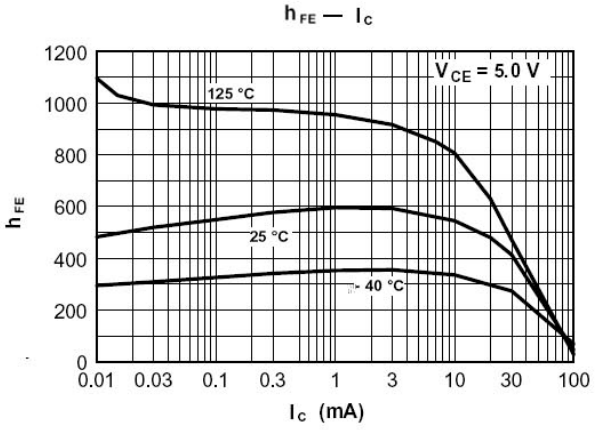
Silicon NPN transistor in a TO-92 Plastic Package.

Low noise, high gain.

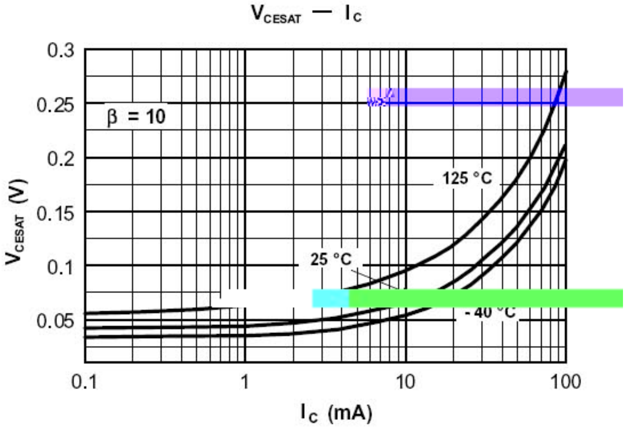
This device is designed for general purpose amplifier applications at collector currents from 1 A to 50

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	4.5	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

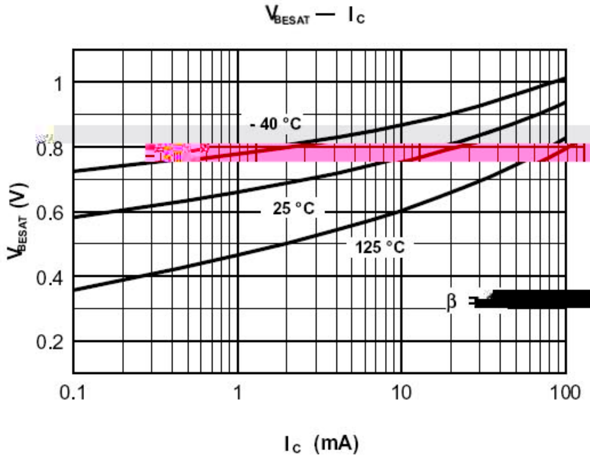
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V	I_E=0			50	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=3V	I_C=0			50	nA
DC Current Gain	$h_{FE(1)}$	V_{CE}=5V	I_C=100 A	300	900		
	$h_{FE(2)}$	V_{CE}=5V	I_C=10mA	300			
	$h_{FE(3)}$	V_{CE}=5V	I_C=1mA	350			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=10mA	I_B=1mA			0.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	I_C					



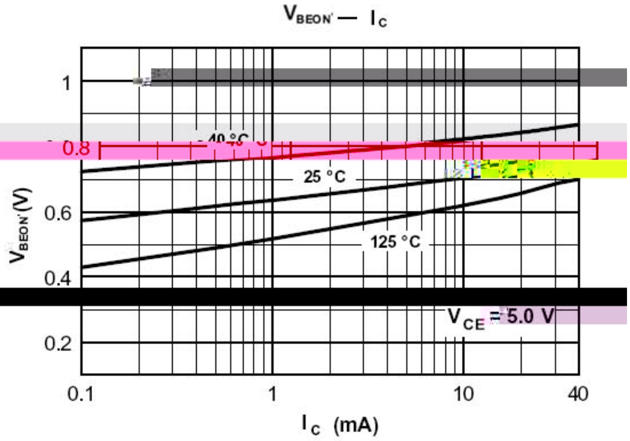
h_{FE} — I_C



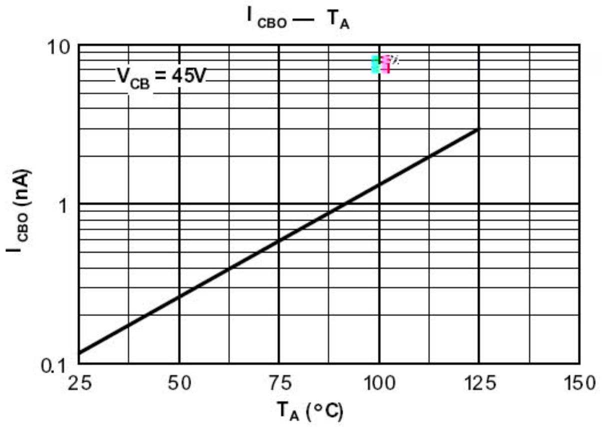
V_{CESAT} — I_C



V_{BESAT} — I_C



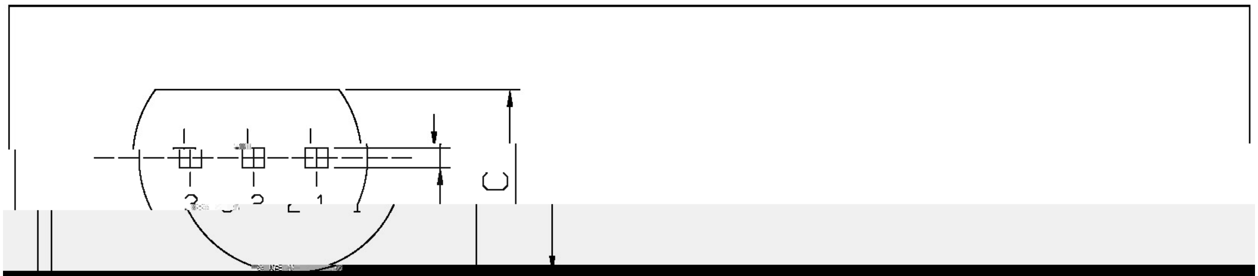
V_{BEON} — I_C



I_{CBO} — T_A

TO-92

Unit: mm



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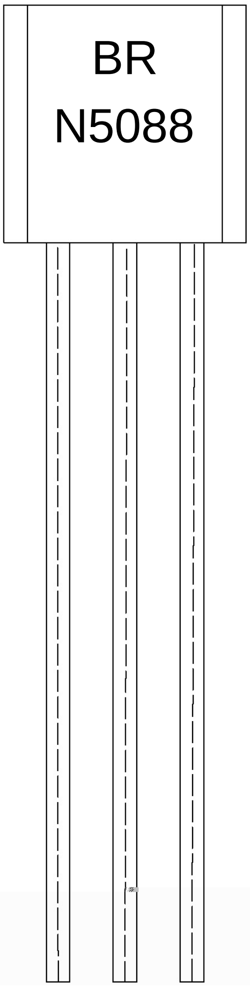
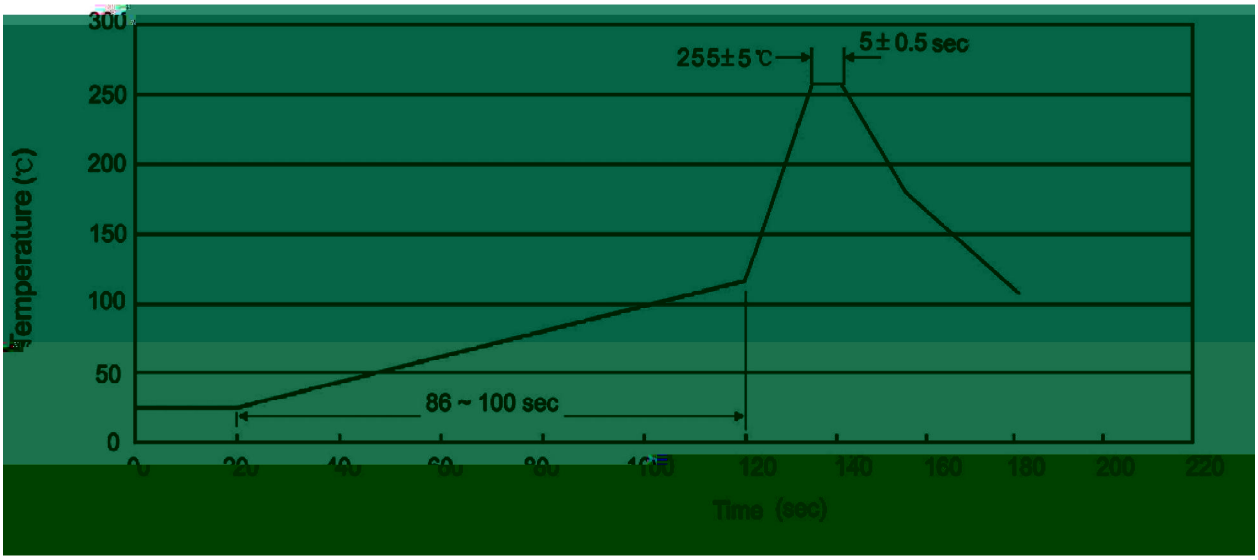


Note:

BR:	Company Code.
N5088:	Product Type.
****:	Lot No. Code, code change with Lot No.



Note:

1 25 150 60 90sec;

2 255 5 5 0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec.

Temp.:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱